



Magnetic structure calculations of $\text{Ir}_{0.5}\text{Mn}_{0.5}$ over- and sub-layer at Co(001) surface

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ABSTRACT

Density functional theory calculations are performed to investigate the magnetic structure of $\text{Ir}_{0.5}\text{Mn}_{0.5}$ chemically alloyed over- and sub-layer at Co(001) surface. $\text{Ir}_{0.5}\text{Mn}_{0.5}$ exhibits ferrimagnetic ordering as the ground state for both systems. Alloyed $\text{Ir}_{0.5}\text{Mn}_{0.5}$ chemically ordered monolayer is found to be more stable at the surface rather than the sub-surface of Co(001). The magnetic moments of Mn surface atoms, Mn_I and Mn_{II} , in $\text{Ir}_{0.5}\text{Mn}_{0.5}/\text{Co}(001)$ over-layer system are found to be $3.49 \mu_B$ and $-3.56 \mu_B$, respectively with intra-layer antiferromagnetic (AFM) coupling. While the Mn_I couples ferromagnetically with Co subsurface moment ($1.68 \mu_B$), Mn_{II} couples antiferromagnetically. $\text{Ir}_{0.5}\text{Mn}_{0.5}/\text{Co}(001)$ system exhibits a magnetocrystalline anisotropy energy (MAE) of -2.8 meV/cell (-0.7 meV/Mn atom), in the direction along [001]. The ferrimagnetic surface ordering and the high MAE of $\text{Ir}_{0.5}\text{Mn}_{0.5}/\text{Co}(001)$ are believed to be promising for potential applications in perpendicular recording media.

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1. Introduction

The exchange bias is a phenomenon that appears at the interface between antiferromagnet (AFM) and ferromagnetic (FM) layers. When these layers are cooled in a magnetic field below Néel temperature (T_N) of the AFM layer, where the Curie temperature (T_C) of the FM layer is larger than T_N [1], a magnetic anisotropy occurs at the AFM/FM interface causing a shift in the magnetic hysteresis loop [2,3]. This interface anisotropy contributes to phenomena such as interlayer exchange coupling, spin-tunneling, and giant magneto-resistance that have found their technological applications in devices such as spin-valve read heads [4] or magnetic random access memory (MRAM) [5].

It has been found that FeMn [6], IrMn [7], NiMn [8,9], MnPt [10], MnPd [11] alloys that possess $L1_0$ geometrical structure have antiferromagnetic ordering with high Néel temperatures. Therefore, they attracted much of the scientific interest due to their promising applications such as exchange-biasing layers. However, low-dimensional overlayers of these alloys adsorbed on substrates such as Cu(001) are found to exhibit $c(2 \times 2)$ chemically ordered structures [12–20]. Therefore, these low-dimensional systems exhibit different magnetic orderings than their bulk.

The AFM alloy that exhibits the highest Néel temperature among Mn-based alloyed systems is IrMn [21], which is considered to be promising for potential applications in recording media. Its interesting properties such as corrosion resistance, high blocking temperature ($T_B = 250^\circ\text{C}$), and small critical thickness have stimulated much interest for experimental investigations [22,23,7]. The effect of decreasing the thickness of IrMn films to the Angström-scale on the exchange bias in spin valves has been investigated by Perdue et al. [24]. They found that the minimum required thickness of the antiferromagnet that retains the exchange bias is 4 \AA . Using soft X-ray resonant magnetic scattering measurements, Hase et al. [25] have found a small magnetic moment on the antiferromagnetic IrMn pinning layer in a NiFe/Cu/Co/IrMn spin valve structure that lies antiparallel to the Co moment.

IrMn has also the highest magnetocrystalline anisotropy energy (MAE) as compared to MnNi, MnPd, MnRh, and MnPt [26]. This fact makes it promising for potential applications in spintronics devices since MAE is believed to be responsible for the exchange bias that shifts the hysteresis loop along the axis of an external field due to the interface coupling of FM and AFM layers. The exchange bias phenomenon has been reported for films of perpendicular easy axis [27–34]. IrMn has proven to be a good candidate to obtain exchange-bias in conjunction with perpendicular magnetic anisotropy, which has been evidenced in Co/Pt multilayers covered with IrMn thin films [7].

In spite of the abundance in the experimental studies for such a thin-film alloy, the theoretical investigations are still scarce. The aim of this paper is to provide a microscopic insight into the electronic and

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